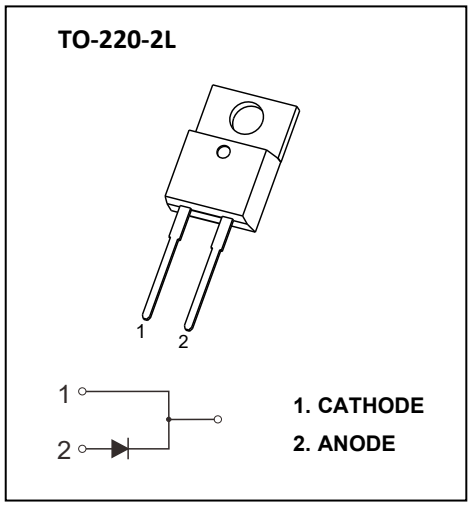
JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD.

TO-220-2L Plastic-Encapsulate Diode

CSD10H65 Silicon Carbide Schottky Diode



MAIN CHARACTERISTICS

I_O	10A(T_C≤127℃)
V_{RRM}	650V
T_j	175℃
$V_{F(typ)}$	1.5V (@T_j=25℃) 2.0V (@T_j=175℃)

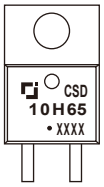
FEATURES

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Temperature-independent performance
- High-speed switching
- Low switching loss
- Low Leakage Current

Application

- Industrial Power Supplies
- Power factor correction
- Motor drive traction
- EV charging station
- Solar Inverters

MARKING



CSD10H65 = Device code
Solid dot = Green molding compound device
if none, the normal device
XXXX = Code

MAXIMUM RATINGS (T_j=25℃ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak repetitive reverse voltage		650	V
V_{RWM}	Working peak reverse voltage			
V_R	DC blocking voltage			
$I_{F(AV)}$	Average Forward Current	T_C≤25℃	21	A
		T_C≤100℃	13	A
		T_C≤127℃	10	A
I_{FSM}	Non-Repetitive peak forward surge current (10ms half sine wave)		56	A
$\int i^2dt$	i^2t value (t_P=10ms)		15.7	A^2s
P_D	Power dissipation		66	W
$R_{\theta JC}$	Thermal Resistance From Junction to Case		2.28	℃/W
T_j	Junction temperature		-55~175	℃
T_{stg}	Storage temperature		-55~175	℃

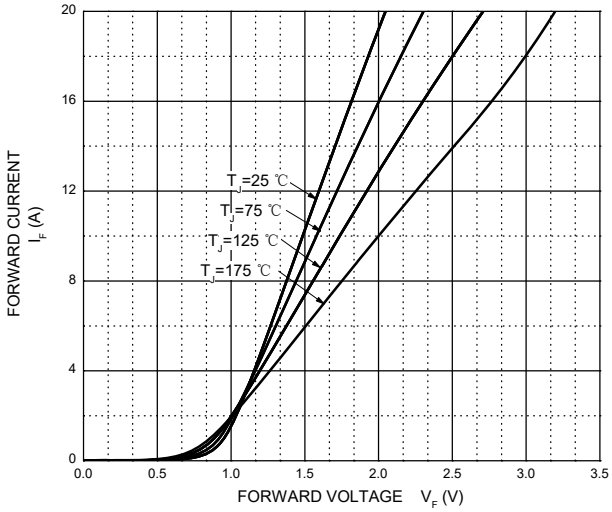
Typical Characteristics

ELECTRICAL CHARACTERISTICS(T_j=25℃ unless otherwise specified)

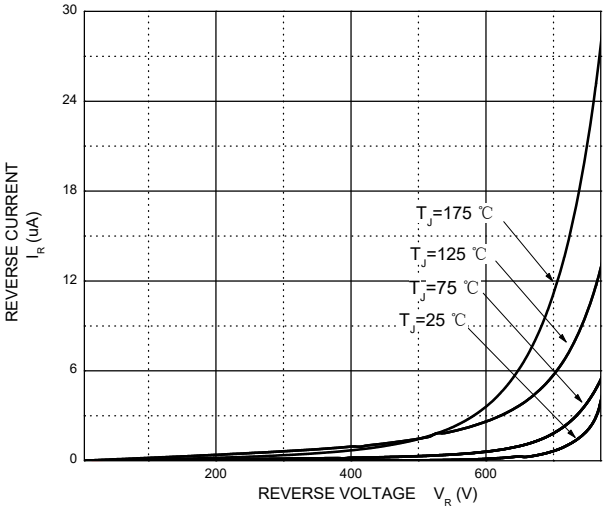
Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=100μA		650			V
Reverse current	I_R	V_R=650V	T_j=25℃		2	20	μA
			T_j=175℃		20	200	μA
Forward voltage	V_F	I_F=10A	T_j=25℃		1.5	1.8	V
			T_j=175℃		2.0	2.4	V
Total capacitance	C	V_R=0V,f=1MHz			380		pF
		V_R=200V, f=1MHz			37		pF
		V_R=400V, f=1MHz			29		pF
Total capacitive charge	Q_C	V_R=400V $Q_C=\int_0^{VR} C(V)dV$			21		nC
Capacitance Stored Energy	E_C	V_R=400V $E_C=\int_0^{VR} C(V)\cdot VdV$			3.2		μJ

Typical Characteristics

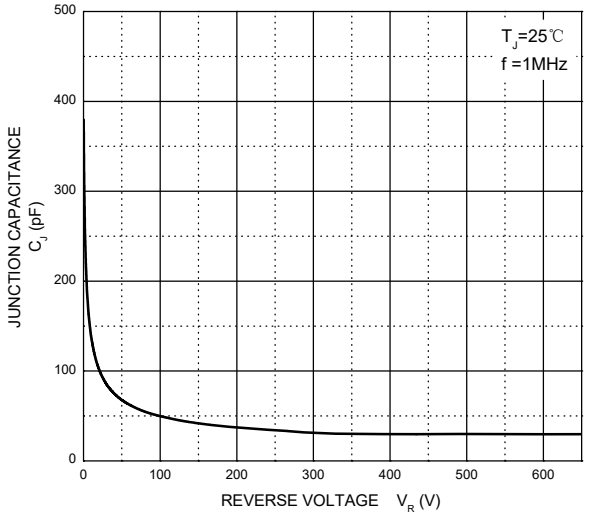
Forward Characteristics



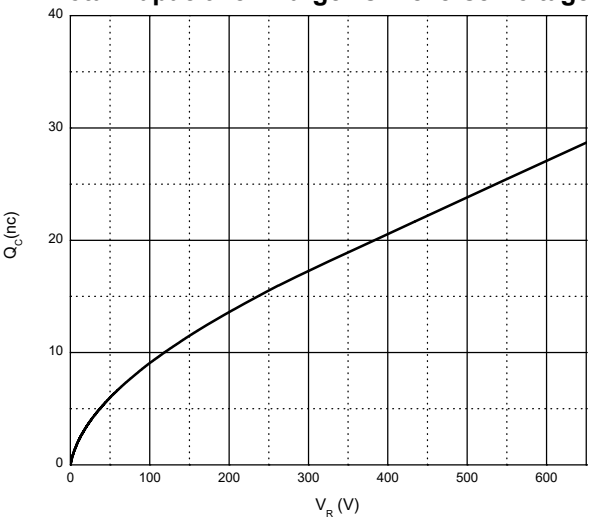
Reverse Characteristics



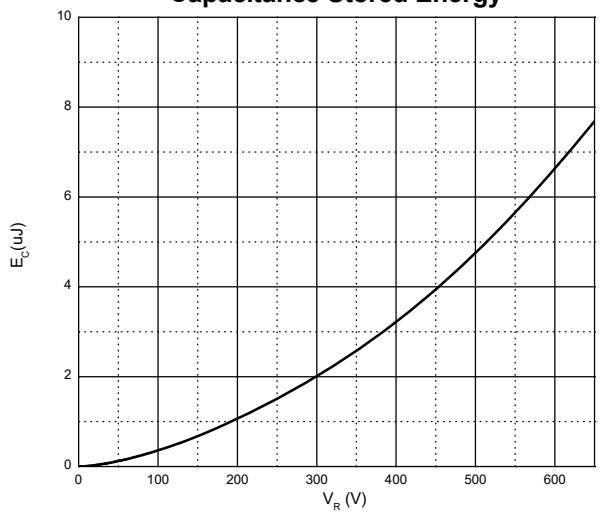
Capacitance Characteristics Per Diode



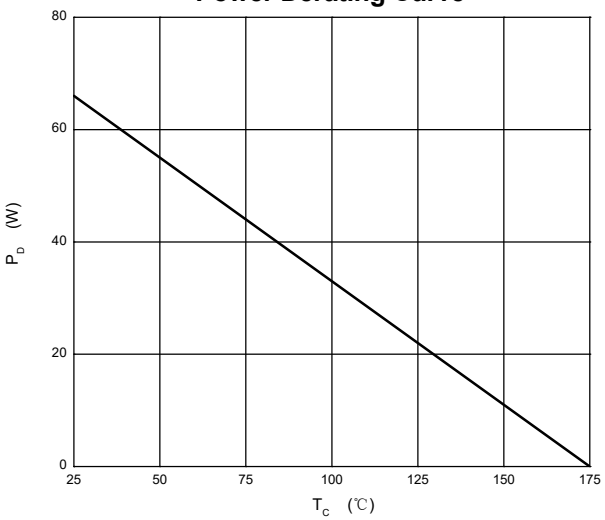
Total Capacitive Charge vs. Reverse Voltage



Capacitance Stored Energy

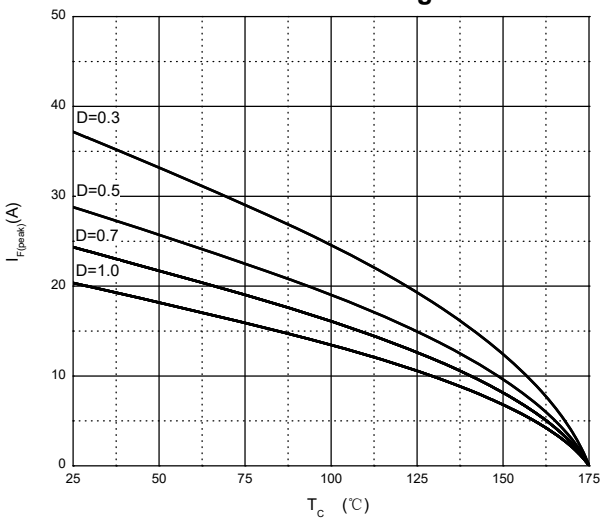


Power Derating Curve

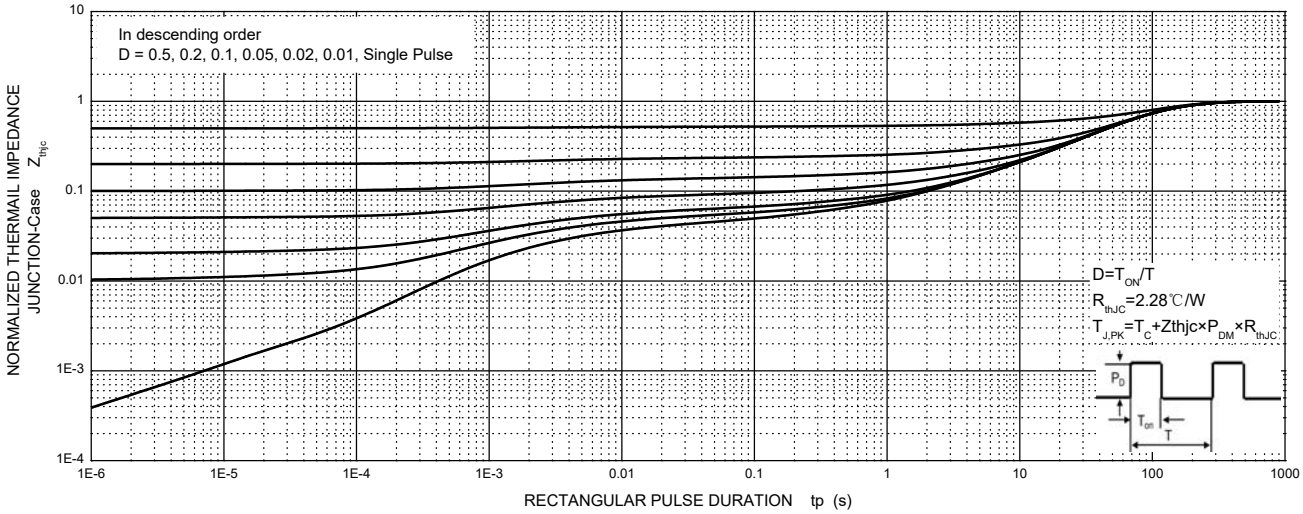


Typical Characteristics

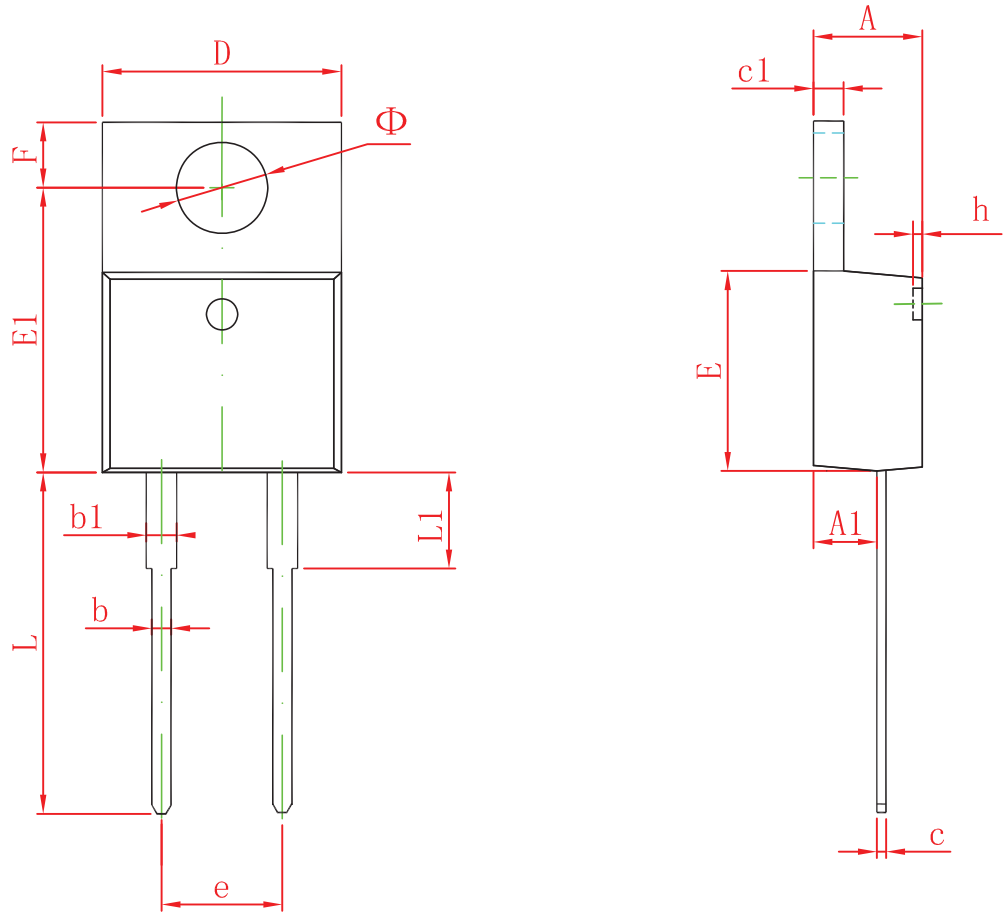
Current Derating



CSD10H65 Transient Thermal Impedance, Junction-Case



TO-220-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.450	4.750	0.175	0.187
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.300	0.500	0.012	0.020
c1	1.170	1.370	0.046	0.054
D	9.830	10.330	0.387	0.407
E	8.500	8.900	0.335	0.350
E1	12.050	12.650	0.474	0.498
e	5.080 TYP		0.200 TYP	
F	2.540	2.940	0.100	0.116
h	0.100 TYP		0.004 TYP	
L	13.300	13.800	0.523	0.543
L1	3.540	3.940	0.139	0.155
Φ	3.735	3.935	0.147	0.155